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ARTICLE

ENABLING HIGH PERFORMANCE n-TYPE METAL OXIDE SEMICONDUCTORS AT LOW TEMPERATURES FOR THIN FILM TRANSISTORS

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Amorphous oxide semiconductors have drawn considerable attention as a replacement for ubiquitous silicon based technologies. By virtue of their flexible substrate compatibility and transparency, amorphous metal oxide semiconductor (AOS) thin film transistors (TFTs) are being explored in emerging flexible/transparent technologies. However, rapid advances in such technologies requires the development of high-performance thin film transistors, which can be fabricated at low processing temperatures. In this review paper we discuss the recent progress made in n-type semiconductor TFTs activated at low temperatures both on rigid and flexible substrates with a focus on the replacement of conventional high temperature annealing. Several low temperature processing approaches that have been reported in both vacuum deposited and solution processed n-type metal oxide semiconductor based thin film transistors are evaluated, with an emphasis on some novel techniques which can effectively modulate the electronic property of the n-type metal oxide semiconductor systems at low temperatures. The final part of this review draws conclusions and discusses the outlook for future research efforts in achieving low temperature activated high performance n-type TFTs.

1. Introduction

Thin-film transistors (TFTs) have been the focus of intense worldwide research during the past decade, with it emerging as a fundamental building block for optoelectronic devices such as flat-panel displays, liquid crystal displays (LCDs) and active matrix organic light emitting diodes (AMOLEDs), wherein they perform a critical function in display operation[1–5]. With the display technology's insatiable demand for higher resolution, larger screen size, lower power consumption and reduced costs, a-Si thin-film transistors has been challenged by low-temperature polycrystalline silicon and metal-oxide TFTs. In comparison to low-temperature poly-Si (LTPS) TFTs, metal oxide TFTs present inherent advantages such as improved large-area uniformity and considerably lower manufacturing cost, while maintaining high carrier mobility, good transparency and reasonable electrical reliability/stability[6,7]. By virtue of their flexible substrate compatibility and transparency, amorphous metal oxide semiconductor (AOS) TFTs are of interest in emergent technologies such as flexible display, flexible transparent circuitry, electronic skin, smart contact lenses and flexible neuromorphic devices (Fig. 1)[8,9]. Metal oxide (MO) semiconductors contain heavy post transition metal cations with $(n-1)\,d^{10}ns^0$ ($n \geq 5$) electronic configurations, where the large radii of the metal ns orbitals leads to adjacent orbital overlap and consequently results in high degree of wave-function overlap, electron delocalization, and relatively high electron mobility, independent of microstructure. As a result, they retain relatively high electron mobility even in the amorphous state thus rendering them an ideal material for high throughput and low cost manufacturing processes [10]. Deposition of these thin films are done either by vacuum techniques such as sputtering, atomic layer deposition (ALD) etc. or by ambient pressure solution based processes such as spin coating or spray pyrolysis. Solution-processed TFTs require relatively higher processing temperatures for optimum film formation, densification, and impurity removal; without which they exhibit relatively low carrier mobilities. Since oxide semiconductor thin films formed at low temperatures exhibit poor electrical characteristics due to the presence of numerous defects and impurities, post-deposition annealing (temperature > 350 °C) is required to modulate their electronic properties for the fabrication of high performance thin film transistors [3,6]. Recently significant effort has been expended to explore new material compositions as well as novel processing methodologies to improve the electronic transport in the metal oxide, and to lower the processing temperature for compatibility with low-cost and flexible polymer substrate materials [8]. New alternatives for activation/improvement of oxide thin film transistor's properties are also being concurrently explored, with research focus currently leaning towards oxygen vacancy modulation of MO semiconductors [3,8]. In this review, we will focus on several low temperature post processing approaches that

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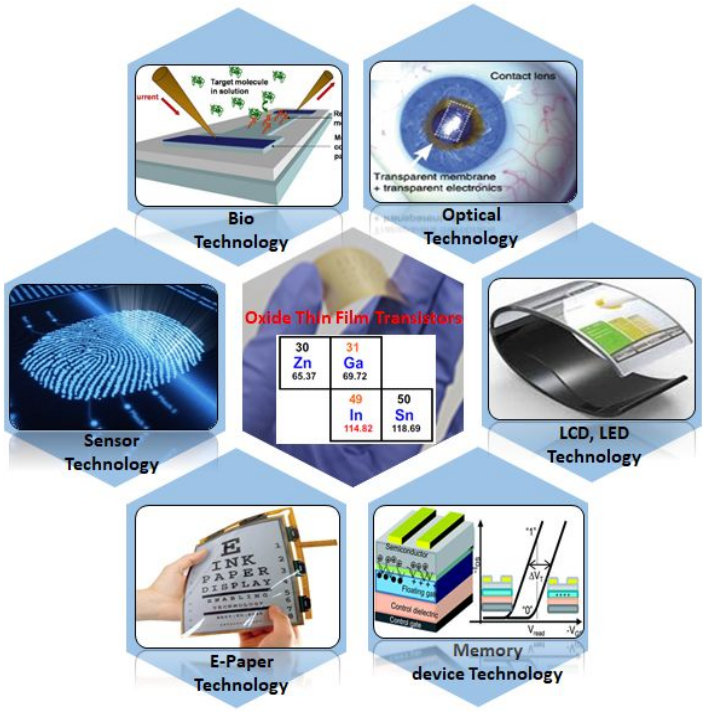

Figure 1. Metal oxides for thin film transistors and their applications in flexible electronics

have been reported in both vacuum deposited and solution processed n-type metal oxide semiconductor thin film transistors, with an emphasis on novel techniques such as ionic liquid activation and capping layers which effectively modulate the electronic property of the n-type metal oxide semiconductor system.

Electronic structure modulation: In 1996 Hosono et al. proposed a multicomponent combination of cations for the design of an amorphous metal oxide semiconductor. The selected cations possess conduction bands derived from large ionic-radius, spherically symmetric 4s, 5s, or 6s electron orbitals from the portion of the periodic table shown inset of Fig. 1. Since then there have been many metal oxide semiconductor trials with the most prevalent ones involving Indium (In), tin (Sn), zinc (Zn), and gallium (Ga) as AOS design starting points. This is because their binary oxides such as indium oxide (In_2O_3), tin-oxide (SnO_2), and zinc oxide (ZnO) are the three most commonly used transparent conducting oxides (TCOs)[11]. These materials have wide band gaps (E_g > 3 eV), high transparency (> 80%) and high electrical conductivity. Additionally, they retain relatively high electron mobility even in the amorphous state and are hence widely considered as the base materials for amorphous MO semiconductors. The small effective masses and corresponding relatively high mobility of these oxides are valued for both TCO and AOS applications. However, these materials suffer from very high carrier concentrations, non-uniformity and high leakage currents. These issues were addressed by mixing two or more metal cations to form ternary or quaternary systems, to boost the formation of amorphous films, thereby reducing the carrier concentration and decreasing the grain boundaries present in polycrystalline samples [10]. For MO TFTs to exhibit a low I_{off}, high I_{on} and stable performance, it is imperative to limit the semiconductor carrier concentration to a low level, preferably < 10^{17} cm^{-3}. In the case of binary or ternary MO systems, moderate n-type doping can be controlled by the cation/anion non-stoichiometry or process optimization. An alternative approach is to introduce an extra component, such as a carrier suppressor (a dopant). Primary requirements for dopants are the following: (i) M-O bond strength should be higher than that of the matrix metal ion (ii) Dopant size should be smaller than the matrix host metal ion; else the dopant will act as a defect site[12] (iii) High Lewis acid strength, since it results in higher mobility via suppression of scattering by oxygen interstitials[13] (iv) An appropriate concentration of dopant to ensure accurate control of the oxygen vacancies without a significant decrease in the mobility. Various elements such as Gallium (Ga), Tungsten (W), Silicon (Si), Hafnium (Hf), Zirconium (Zr), Titanium (Ti), Aluminum (Al) and Tantalum (Ta) have been studied and shown to exhibit carrier suppressor behavior[13]. Therefore, the cation composition can be modified to improve the stability of transparent metal oxide (TMO) TFTs under bias and illumination stress. In addition, incorporation of nitrogen in the binary systems also appears to suppress the growth of indium oxide and zinc oxide resulting in nanostructured phase[14]. The substitution of an oxygen anion with a nitrogen anion effectively passivates the V_O sites in ZnO and In_2O_3 by eliminating the oxygen deficiency related deep levels near the valence band maximum thereby improving the photo bias stability[14,15]

Processing methods: Electronic and optoelectronic devices based on metal oxides usually comprise of thin films deposited on appropriate substrates. High-quality metal oxide network can be obtained by using extremely controlled deposition processes like pulsed laser deposition (PLD), Atomic layer deposition (ALD) and even by using less sophisticated methods like radiofrequency (RF) magnetron

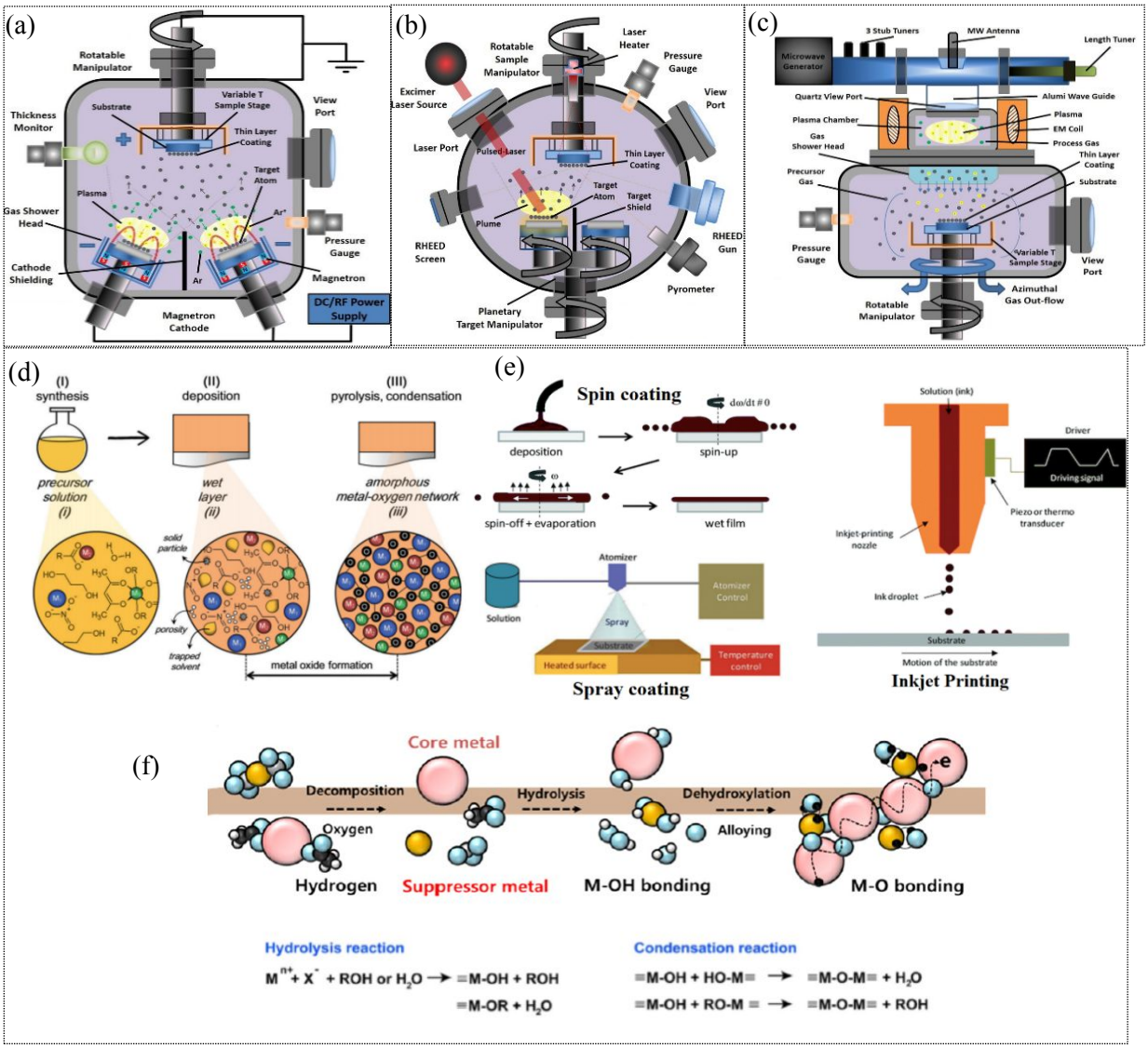

Figure 2. Low-cost deposition techniques used to produce electronic devices based on semiconducting metal oxides. **(a)** RF magnetron sputtering **(b)** Pulsed laser deposition (PLD) **(c)** Atomic layer deposition (ALD).[16] **(d)** Stages of solution processing of metal oxide films[155] **(e)** Deposition techniques[155] **(f)** Schematic of the evolution of metal oxide films through precursor route film deposition and subsequent anneal.

sputtering as depicted in Fig. 2a-c. These techniques permit the growth of high-quality uniform thin films with atomic layer precision.[16] Solution processing is another widely adopted method for fabricating MO films for TFT applications and is appealing in terms of low cost, scalability and compatibility with high throughput manufacturing. Fig. 2d illustrates the stages involved in solution processing, namely, the synthesis of the solution, deposition of the solution on substrates followed by pyrolysis or condensation for MO formation. The evolution of the film as it proceeds through these stages are also illustrated. The various deposition techniques employed, such as spin-coating, inkjet printing and spray coating are presented in Fig. 2e. Nanoparticle route and precursor route are two widely adopted approaches for synthesis of the solution for metal oxide film formation. Nanoparticle route is a straightforward approach wherein a metal oxide nanoparticle dispersion in appropriate solvent is deposited on the substrate. The evolution of metal oxide films deposited through the precursor route is depicted in Fig. 2f, where the metal cation complexes formed by the solvation of metal precursors, undergo hydrolysis and condensation reactions to form metal-oxide (M-O) network. Although nanoparticle approach seems advantageous in terms of low temperature processing, the inherent porous nature affects the film quality and the particle boundaries limiting charge transport which severely impairs the device characteristics of the fabricated TFTs[17]. In comparison, the precursor route aids in the formation of denser, grain boundary-free MO films with lower surface roughness. However, it needs to be noted that high the formation of denser, grain boundary-free metal oxide films with lower surface roughness. However, a high temperature anneal is generally a prerequisite for the formation of high-quality metal oxide films since it allows for effective and complete hydrolysis, condensation and densification reactions which are imperative for the formation of M-O-M network and for the removal of organic residues.

Table 1. n- type TFTs processed at low temperature.

Material	Technique	(Tdep./Tpost.)/ (℃)	Substrate	Dielectric	Mobility ($cm^2V^{-1}s^{-1}$)	On/off ratio	
Metal oxide TFTs on rigid substrates							
In_2O_3	evaporation	200	Silicon	SiO_2	27	10^4	[18]
IZO	sputtering	-	Glass	SiO_x	157	10^{10}	[19]
IWO	sputtering	150	Silicon	SiO_2	39	10^{10}	[20]
IWO	sputtering	100	Silicon	SiO_2	36.7	10^7	[21]
IWO	sputtering	100	Silicon	SiO_2	27.55	10^8	[22]
IWO/IWO:N	sputtering	100	Silicon	SiO_2	27.2	10^7	[23]
IWZO	Sputtering	300	Silicon	SiO_2	22.30	10^8	[24]
IZTO	ALD	180/350	Silicon	SiO_2	27.8	10^{11}	[25]
IGZO	ALD	/250	Silicon	SiO_2	22.1	10^8	[26]
IGZO	sputtering	300/ 240	Silicon	SiO_2	14.72	10^9	[27]
IGZO	sputtering	150/New	Silicon	SiO_2	12.68	10^8	[28]
IGZO	sputtering	RT/350	Silicon	SiO_2	11.2	10^8	[29]
IGZO	sputtering	RT/300	Silicon	SiO_2	9.21		[30]
AIZO	sputtering	225	Silicon	SiO_2	20.65	10^7	[31]
AIZO	sputtering	RT	Glass	SiO_2	5.67	10^6	[32]
ITO/ATZO	sputtering	-	Glass	SiO_2	246	10^8	[33]
ZNON	sputtering	Light Irradiation	Silicon	SiO_2	48.4	10^9	[34]
InON	sputtering	300	Silicon	SiO_2	9.55	10^7	[15]
SnO_2	sputtering	180	Silicon	HfO_2	92	10^6	[35]
In_2O_3	ALD	300	Glass	Al_2O_3	41.8	10^7	[36]
In_2O_3	ALD	160/300	Silicon	Al_2O_3	7.8	10^7	[37]
ZnO	ALD	/200	Silicon	Al_2O_3	27.8	10^9	[38]
IZO	sputtering	300	Glass	$SiN_x/p\text{-}SiO_x$	50.4	10^{10}	[39]
IZO/HIZO	sputtering	250	Glass	SiN_x/SiO_x	48.28	10^7	[40]
PrIZO	sputtering	300	Glass	SiO_2/Si_3N_4	26.3	10^8	[41]
IZO/IZO:Si	sputtering	300	silicon	SiO_2	15.30	10^8	[42]
IZO/ZnO/IGZO	Sputtering	300	silicon	SiO_2	14.0	10^8	[43]
ITO	sputtering	200	Glass	Al_2O_3	56.1	10^9	[44]
ITO	sputtering	250	Glass	Al_2O_3	25.9	10^9	[45]
IGO	ALD	200/300	Glass	Al_2O_3	9.45	10^8	[46]
IGO	sputtering	RT	Glass	Al_2O_3	2.66	10^6	[47]
IGZO	sputtering	RT/200	Silicon	HfO_2	38.29	10^6	[48]
IGZO	sputtering	RT/100	Silicon	SiN_X	26.03	10^7	[49]
IGZO	sputtering	70	Silicon	Al_2O_3	6.3	10^7	[50]
IGZO	sputtering	RT	Glass	Al_xO_y	5.4	10^6	[51]
IGTO	sputtering	150	Glass	PVP-co-PMMA, PMF, HfO_x	25.9	10^7	[52]
HIZO	sputtering	300	Glass	SiN_x/SiO_2	13.73	10^{12}	[53]
Metal oxide TFTs on flexible substrates							
ZnO	ALD	100 /	PET	Al_2O3	37.1	10^7	[54]
ZnO	PEALD	200/–	PI	Al_2O_3	12	10^8	[55]
ZnO	sputtering	RT/RT	PEN	Al_2O_3	11.56	10^8	[56]
ZnO	sputtering	100/–	PET	HfO_2	7.95	10^8	[57]
ZnO	hydrothermal	90/100	PET	PMMA	7.53	10^4	[58]
ZnO	spin-coating	–/160	PEN	Al_2O_3-ZrO_2	5	10^4	[59]
ZnO	ALD	150/–	PI	Al_2O_3	3.07	10^2	[60]

ZnO	printing	–/250	PI	ion-gel	1.67	10^5	[61]
ZnO	sputtering	–/225	PI	HfO_2	1.6	10^6	[62]
ZnO	sputtering	–/MW	PES	Al_2O_3	1.5	10^6	[63]
ZnO	sputtering	RT/350	PDMS	SiO_2	1.3	10^6	[64]
ZnO	spin-coating	RT/200	PI	SiO_2	0.35	10^6	[65]
ZnO	spin-coating	–/150	PES	hybrid	0.142	10^4	[66]
ZnO	spin-coating	–/200	PET	c-PVP	0.09	10^5	[67]
ZnO	spin-coating	–/135	PEN	RSiO1.5	0.07	10^4	[68]
ZTO	Inkjet-print	30/300	PI	ZrO_2	0.04	10^3	[69]
IZO	sputtering	RT/RT	PET	SiO_2	65.8	10^6	[70]
IZO	spin-coating	RT/280	PI	Zr-Al_2O_3	51	10^4	[71]
IZO	sputtering	–/300	PI	Al_2O_3	6.64	10^7	[72]
IZO	SCS	275/–	polyester	Al_2O_3/ZrO_2	3.9/6.2	10^4	[73]
IZO	spin-coating	RT/350	PI	K-PIB	4.1	10^5	[74]
IZO:F	spin-coating	RT/200	PEN	Al_2O_3	4.1	10^8	[12]
IWO	sputtering	270	PI	Al_2O_3	25.86	10^5	[75]
ZITO	PLD	RT/–	PET	v-SAND	110	10^4	[76]
ZITO	sputtering	300/200	PI	SiO_2	32.9	10^9	[77]
ZITO	sputtering	RT/–	polyarylate	Al_2O_3	16.93	10^9	[78]
IGZO	spin-coating	RT/350	PI	Al_2O_3	84.4	10^5	[79]
IGZO	sputtering	RT/RT	PC	$SiO_2/TiO_2/SiO_2$	76	10^5	[80]
IGZO	sputtering	RT/200	PI	HfLaO	22.1	10^5	[81]
IGZO	sputtering	RT/200	PDMS	P(VDF-TrFE)	21	10^7	[82]
IGZO	sputtering	200/220	PI	SiO_2	19.6	10^9	[83]
IGZO	sputtering	RT/–	PI	Al_2O_3	17	10^5	[84]
IGZO	sputtering	RT/180	PEN	Al_2O_3	15.5	10^9	[85]
IGZO	sputtering	–/180	PEN	Si_3N_4	13	10^8	[86]
IGZO	sputtering	150/150	PEN	Al_2O_3	12.87	10^9	[87]
IGZO	sputtering	–/160	PEN	Al_2O_3	11.2	10^9	[88]
IGZO	spin-coating	–/PN254 nm	PI	ZAO	11	10^9	[89]
IGZO	sputtering	RT/110	PET	c-PVP	10.2	10^6	[90]
IGZO	sputtering	RT/150	PVA	SiO_2/Si_3N_4	10	10^6	[91]
IGZO	sputtering	–/300	thin glass	Si_3N_4	9.1	10^8	[92]
IGZO	sputtering	RT/190	PEN	SiO_2	8	10^7	[93]
IGZO	sputtering	–/PN254 nm	PAR	Al_2O_3	7	10^8	[94]
IGZO	spin-coating	–/PN254 nm	PI	Al_2O_3	5.41	10^8	[95]
IGZO	sputtering	RT/–	PI	Al_2O_3/SiO_2	4.93	5	[96]
IGZO	sputtering	RT/–	PI	PVP	3.6	10^4	[97]
IGZO	sputtering	RT/–	PEN	PVP	0.43	10^5	[98]
IGZO	sputtering	RT/200	PDMS	P(VDF-TrFE)	0.35	10^4	[99]
IGZO/IZO	sputtering	40/200	PEN	SiO_2	18	10^9	[100]

Table 1 summarizes the recent progress made on n-type metal oxide TFTs processed at temperatures below 400 °C. The table lists a selection of MO TFTs fabricated on rigid substrates, which is further divided into TFTs that use SiO_2 dielectric and those employing high-k dielectrics. The table also lists a selection of MO TFTs fabricated on flexible substrates. The technique used for the MO film formation and the processing and post processing anneal temperatures (where applicable) are listed for each, together with important figures of merit of TFT performance (the mobility and on/off ratio). The materials are listed in the order of binary, ternary and quaternary metal oxide systems with the TFT reports arranged according to decreasing mobility values. In general the following observations can be made : (i) Mobilities above 10 can be achieved in metal oxide TFTs even at low processing temperatures, (ii) TFT performance is more robust on rigid substrates when compared to those on flexible substrates, (ii) Vacuum processed metal oxide films are superior in quality and hence leads to overall enhanced device characteristics and (iv) High-k dielectrics with their higher gate capacitance and interface quality results in devices with high mobility at low operation voltages.

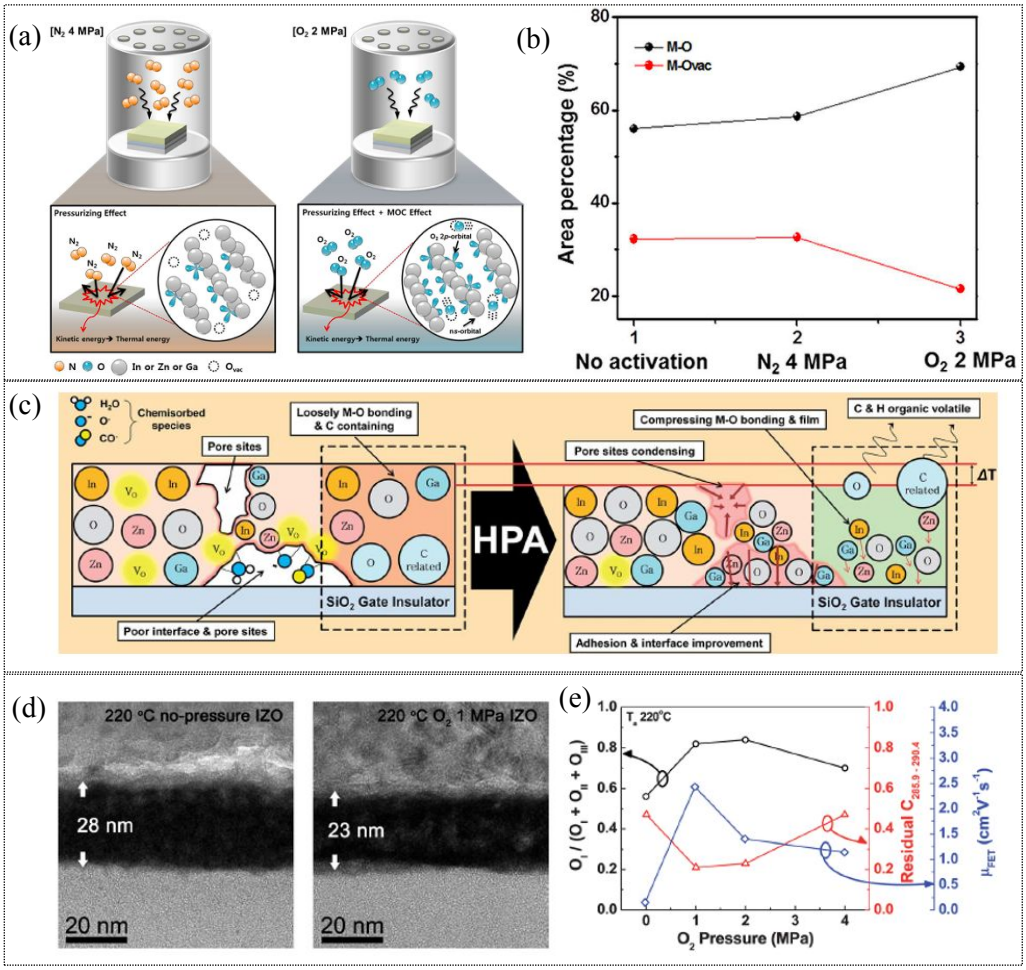

Figure 3 **(a)** Schematic of the effect of N_2 and O_2 HPA on sputtered IGZO films[101] **(b)** Area ratio of M-O and M-O_{vac} for various conditions[101] **(c)** Illustration of the effect of high pressure on low temperature solution - processed metal oxide thin films.[103] **(d)** Cross-sectional HRTEM image of IZO thin film annealed at 220°C (right) and at 220°C in 1 MPa O_2.[103] **(e)** The $O_I/O_I + O_{II} + O_{III}$ ratio, residual carbon ratio (286.1 + 287.1 + 288.1 + 288.9 eV/284.6 eV), and field-effect mobilities as functions of O_2 pressure[103].

2. Low-temperature route for n-type metal oxide semiconductors

Previous studies have proven that the MO films annealed at high temperature (> 400 °C) exhibited good TFT device characteristics. However, low-temperature processing (< 400 °C) is indispensable for realizing AOS TFTs for flexible electronic applications and a low thermal budget post deposition anneal (PDA) process is required to minimize the production cost. In this context conventional thermal annealing (CTA), which has been generally adopted for the PDA process, is disadvantageous in terms of the duration and high thermal budget required. Herein we discuss the various approaches reported, broadly divided into physical and chemical routes, to reduce the processing temperature for the fabrication of metal oxide based TFTs.

2.1 Physical routes for the reduction of process temperature

2.1.1 High pressure annealing

High pressure annealing (HPA), has been recently reported as a promising alternative to CTA for the formation of high-quality metal oxide films. HPA is effective in the activation of sputtered films, as in the case of IGZO reported by Kim et.,al [101]. The mechanism of activation by employing N_2 and O_2 high pressure activation is illustrated in Fig. 3a. Here, the temperature necessary for activation was reduced from 300 to 100°C with the incorporation of HPA in N_2 and O_2 gases, where the kinetic energy of the gas molecules provide the activation energy required, while the incorporation of O_2 gas provides the additional benefit of elevating the metal oxide construction aids by ensuring sufficient *ns* metal orbital overlap for efficient charge transport while simultaneously reducing the electron trap density at lower pressure as evident in in Fig. 3b. This results in TFTs with higher bias stress stability and higher mobility (~11 $cm^2 V^{-1} s^{-1}$) at a low temperature of 100°C compared to TFTs annealed at 300°C. In the case of solution processed metal oxide films, HPA requires lower fabrication temperature compared to CTA methods as it reduces the Gibbs free energy and decomposition temperature for the formation of metal oxide network, with minimal organic residues[102]. In addition, employing HPA also produces denser MO films due to the drastic reduction of porosity, a bane, especially for low temperature solution processed MO films (Fig. 3). Definitive work on HPA annealing has been done by Kim et al, and in 2012 they

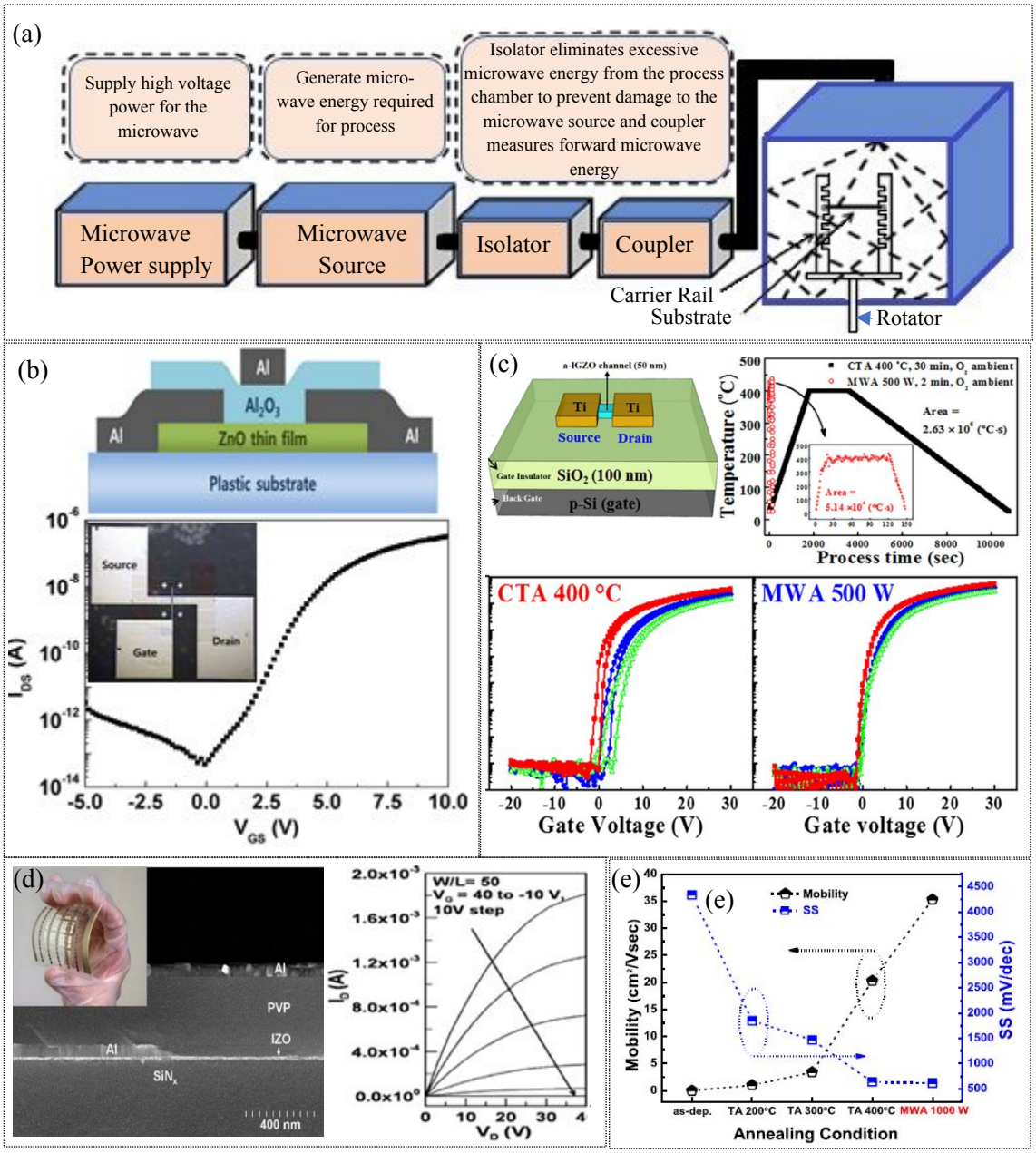

Figure 4. **(a)** The schematic of microwave annealing system[156]. **(b)** schematic of the flexible ZnO TFT and transfer characteristic of microwave processed flexible device[63]. **(c)** Schematic diagram of back-gate top-contact structure a-IGZO TFTs, temperature profile of the annealing process using CTA at 400°C for 30 min in O_2 and MWA at 500W for 2 min in O_2, respectively and transfer characteristics of microwave and CTA processed devices[107]. **(d)** SEM local cross-sectional image of the flexible a-IZO TFT device on the PI substrate; the inset shows a flexed 5 cm×5 cm PI substrate with 27 a-IZO TFT devices and output characteristics[110]. **(e)** Field-effect mobility (μ_{EF}) and subthreshold swing (SS) of 5 nm thick UTB SnO_2 TFTs annealed by different conditions[106].

demonstrated a solution processed IZO TFT on polyimide (PI) substrate subjected to 1MPa HPA in O_2 atmosphere at 220°C [103]. The reduced bulk defects and charge traps provided by HPA also resulted in more stable devices as indicated by the positive bias stress with the lowest V_{th} shift obtained for 1MPa O_2 HPA. Though promising as a CTA replacement, the scalability issues of utilizing HPA for metal oxide layer activation for TFT applications needs to be addressed as a facile integration of this activation method into a roll-to-roll production process flow may prove to be challenging.

2.1.2 Microwave annealing approach

Microwave assisted annealing (MWA) technique has attracted significant attention due to the volumetric heating involved, that directly and uniformly delivers thermal energy to the MO film, while enabling low thermal budget and fast processing, primarily due to the short exposure duration[63,104–108]. In principle, Microwaves compromise with rapid change in electric and magnetic field as well (Fig. 4a). The microwave will heat any material with mobile electric charges such as ions in dielectrics. As example, polar solvents are heated due to interaction of the time varying fields with the polar molecules. As a result, the polar molecules tend to vibrate with the fields and lose energy in collisions. Charges such as ions or electrons within the semiconducting and conducting materials constitute

electric current in response to the field and resulting loss in energy through resistive heating and dielectric relaxation of the materials. In particular, the resistive heating/ohmic loss dominates at lower frequencies (< 10 GHz). Thus MWA process has been shown to provide a lower temperature process that results in good activation[109]. In 2010 T. Jun et al., demonstrated comparison between hot plate annealing and microwave annealing effect on the performance of solution processed ZnO TFT. The microwave-annealing for 30 min at 140℃ of ZnO TFTs on rigid substrate showed better field effect mobility of 1.7 $cm^2 V^{-1} s^{-1}$ compared to hot plate annealed (0.32 $cm^2 V^{-1} s^{-1}$) ones. Additionally, transistors on flexible substrates exhibited device characteristics of 0.57 $cm^2 V^{-1} s^{-1}$. Microwave annealing reduces the grain boundaries due to increase in size of the ZnO nanoparticles and leads to improved transport properties of the charge carries, resulting in better performance of the TFT[104]. In 2014, S. Park et al. also investigated the effect of microwave annealing on sputtered ZnO TFT (Fig. 4b). The microwave irradiation of 2.45 GHz at 700 W for 15 min increased the field effect mobility from 0.2 to 1.5 $cm^2 V^{-1} s^{-1}$ and on/off current ratio from 36.5 to 6.9 $x10^6$. The microwave irradiation induces a large number of oxygen vacancies as confirmed by photoluminescence, resulting in enhanced mobilities[63]. H.-C Cheng also demonstrated microwave annealed solution processed flexible a-IZO TFT[110] with a mobility of 6.9 $cm^2 V^{-1} s^{-1}$, and I_{ON}/I_{OFF} ratio greater than 10^6 (Fig. 4d). In 2014, Lee et al. demonstrated a high reliable microwave assisted annealed a-IGZO thin-film transistors to be used as biosensors. The microwave irradiation of 2.45 GHz at 1000 W for 10 min improved the TFT performance (μ_{FE} = 9.51 $cm^2 V^{-1} s^{-1}$, V_{th} = 0.99 V, I_{ON}/I_{OFF} = 1.18 x 10^8), compared to furnace-annealed a-IGZO TFTs at 400 °C for 30 min (μ_{FE} = 4.51 $cm^2 V^{-1} s^{-1}$, V_{th} = 4.85 V, I_{ON}/I_{OFF} = 3.38 x 10^7). The microwave annealing eliminated the defect density inside the a-IGZO film and improved the device performance. In addition, the microwave-assisted annealed TFT displayed excellent sensing properties in terms of pH sensitivity, reliability, chemical stability when employed as a transducer in an extended-gate ion-sensitive field-effect transistor biosensor.[105] In 2015, K.-W. Jo and his co-workers developed ultra-thin (5 nm) SnO_2 TFTs. The performance of the TFT was significantly improved with field effect mobility of 35.4 $cm^2 V^{-1} s^{-1}$, I_{ON} / I_{OFF} = 4.48 x 10^7 under microwave irradiation of 2.45 GHz at 1000 W for 15 min assisted annealing as compared to CTA (400 ℃, 30 min) TFTs (μ_{FE} = 20.3 $cm^2 V^{-1} s^{-1}$, I_{ON}/I_{OFF} = 2.76 x 10^7) as depicted in Fig. 4e. This result is due to enhancement of crystallinity and elimination of defects in SnO_2 TFTs by the microwave irradiation.[106] In 2019, Shin reported the microwave-assisted annealing of various compositional ratios of sputtered IGZO films in O_2 ambient (Fig. 4c). The temperature of the a-IGZO TFTs samples was measured by an infrared thermometer during the MW-PDA process and observed to be 399.6 ℃ on average. However CTA at 400℃ yielded poorer performance since MWA results in lowered defect densities (D_{it}, N_t) and sub-gap density of state (DOS) [107]. Compared to conventional annealing techniques, the novel microwave annealing techniques facilitate low temperature activation of devices on flexible substrate and may be promising for roll to roll processing of flexible electronics [108].

2.1.3 Photo activation

Photo activation is the most prevalent substitute for thermal annealing of MO films, especially for solution processed MO films, where the light source provides photothermal energy sufficient to initiate the chemical conversion for the formation of metal oxide network. Photoactivation has been demonstrated with deep UV irradiation as a viable annealing technique for the formation of MO films such as IZO, IGZO and IO. Recently, there have been reports on the use of other sources including infrared and intense pulsed light for activation of metal oxide film for TFT applications[111112113]. Deep UV (DUV) irradiation provides sufficient energy for the decomposition, condensation and densification reactions and results in MO films with properties comparable to high temperature CTA MO films (mechanism of activation is illustrated in Fig. 6a). In 2012, Park et al demonstrated the use of DUV irradiation, specifically suitable for nitrate precursors (compared to acetate or chloride precursors) by virtue of their stronger absorption of UV irradiation[114]. Though there is inherent heating to around 150°C during photoactivation, which may aid in the removal of organic residues, this is insufficient as an independent thermal energy source for the formation of M-O-M network, as is evident in Fig. 5b. Though initially demonstrated in inert atmosphere, UV photochemical activation was shown to be equally effective in ambient conditions as reported by Mathews et al [115]. Here, the mid-UV range source with emission spectra of 200 to 300 nm, corresponding to 398.48 to 598.2 kJ/mol was used to ensure decomposition of precursors and initiate the condensation and densification for the formation of high quality InO and IZO films and TFT mobilities of ~ 30 $cm^2V^{-1} s^{-1}$. On the other hand, infrared irradiation activation, relies on the rapid photo thermal effect provided by IR irradiation (Fig. 5c). IR irradiation increases the free energy of the precursor system, elevating it to a metastable state, which reduces the activation energy necessary for the formation of oxide network. Thus, in comparison to conventional thermal annealing, with adequate duration of IR irradiation, lower temperature is sufficient for complete precursor decomposition and metal oxide network formation. This results in metal oxide films with higher carrier concentration and lower defect density due to improved interface quality and higher oxygen vacancy generation. Wang et al, reported that IGZO TFT fabricated by IR irradiation (induced temperature of 230°C) in ambient environments could achieve a mobility 60 $cm^2 V^{-1} s^{-1}$, an I_{ON}/I_{OFF} ratio of 10^6 [111]. This was a marked improvement in mobility compared to conventional high temperature (450°C) annealed IGZO TFT. The higher M-O bond content and oxygen vacancies and lower M-OH content and trap density demonstrated by the IR irradiated MO layers in comparison to thermally annealed counterparts are indicative of high quality, low defect content metal oxide layer with good interface quality which manifests in the high stability exhibited during positive bias stress test (Fig. 5d). Unlike UV annealing, IR irradiation is also effective with chloride precursors (which typically require > 400°C anneal). Xia et al, have reported the use of IR irradiation to form both the AlO_x solution processed dielectric and the IO film employing chloride precursors[112]. The resultant AlO_x dielectric demonstrated properties

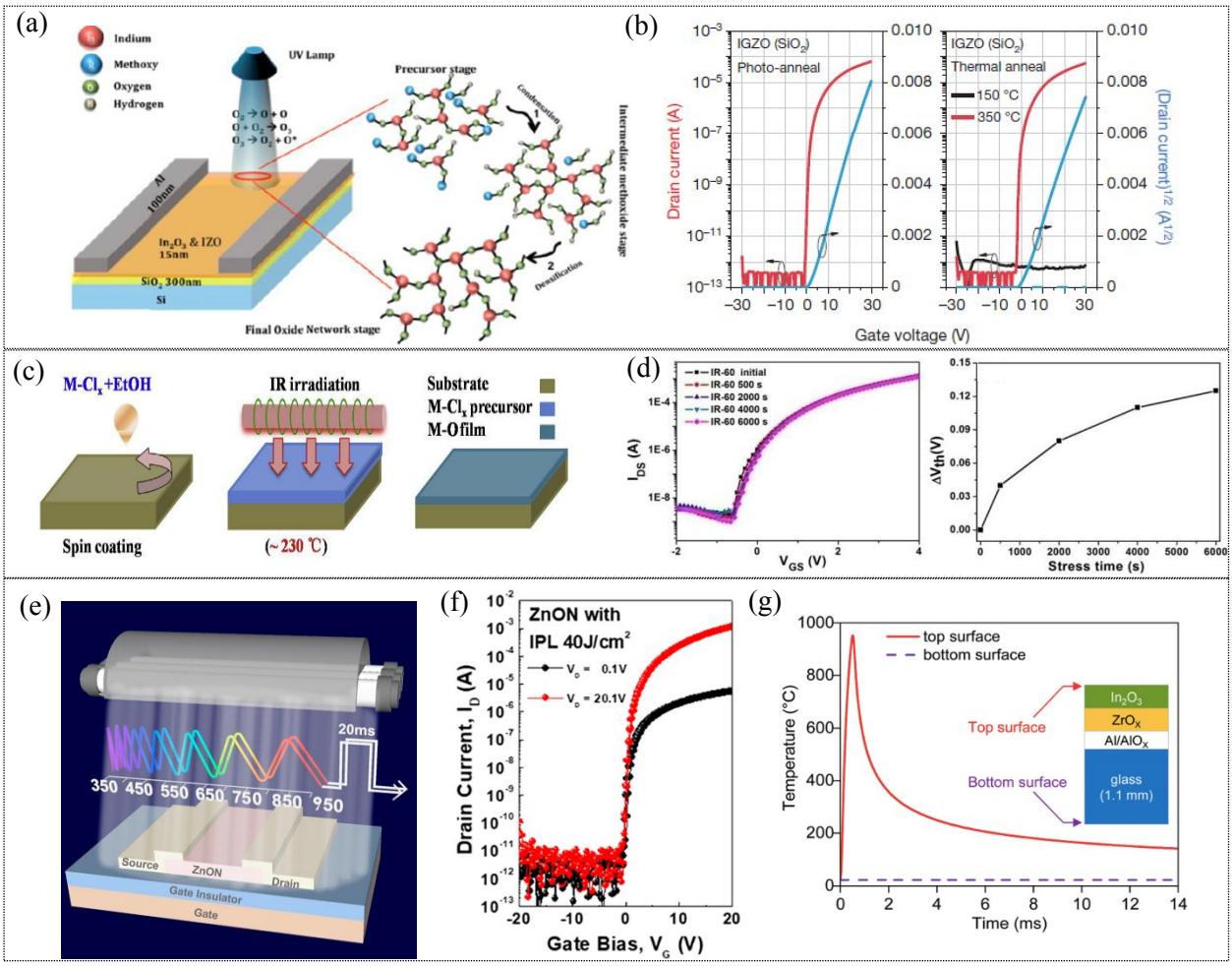

Figure 5. **(a)** Proposed mechanism for photochemical activation via UV irradiation[115]. **(b)** Transfer and output characteristics of photo-annealed and thermally annealed (150 and 350°C) IGZO TFTs[115] **(c)** Process flow of IR irradiation activation for formation of metal oxide film[112] **(d)** Transfer characteristics and Vth shift results of positive bias stress on IGZO TFTs activated by IR irradiation[111] **(e)** Illustration of sub second exposure of IPL(xenon flash lamp) for activation [117] **(f)** Transfer characteristics of IPL activated ZnON TFTs at different drain voltages[117] **(g)** Simulation results obtained using the SimPulse software of the temperature at the top and at the bottom of the In_2O_3 TFT fabricated on a 1.1 mm-thick glass substrate after exposure to xenon light pulse[116]

comparable to vacuum processed counterparts with capacitance of 158 nFcm^{-2} and a small leakage current (5.4 Å~10^{-8} Acm^{-2}) by virtue of the low defect density of IR irradiated films. The IO TFTs exhibited a mobility of around 33 cm^2 V^{-1} s^{-1}. However, the incidental temperature on substrate during IR radiation is higher than that generated during UV irradiation, which may make it unsuitable for certain flexible substrates. The primary advantage of other novel photoactivation sources such as intense pulse light is the sub second exposure duration necessary for the activation of the metal oxide films which ensures selective heating of the precursor film. Intense pulsed light (IPL) using xenon light source was used for the photo activation for solution processed MO films such as IGZO and In_2O_3 TFT and In_2O_3/ZnO heterojunction for TFT applications[113116]. It was also used for the activation of sputtered ZnON films, where a 20ms pulse of 40 J/cm^2 resulted in a TFT devices with high stress stability and a mobility of around 48 cm^{2}V^{-1} s^{-1}[117]. Even though the incidental heating can be as high at 1000 ℃ during exposure in the case of xenon flash lamp, the sub second (500 µs-20 ms) exposure duration ensures negligible heating of the substrate (Fig. 5g)[116]. In_2O_3 TFTS were fabricated on polyimide (PI), and heat-stabilized polyethylene naphthalate (PEN) substrates using xenon lamp photonic activation, demonstrating its compatibility with flexible substrates[118].

Sections 2.1.1 -2.1.3 discussed the widely reported alternatives to CTA. However, there is always an inherent and unavoidable thermal component involved and a few of the discussed post deposition treatments are not compatible with all flexible substrates. Recently, there have been studies on other novel physical techniques which effectively modulate the oxygen vacancies/electronic structure of MO films athermally, with the additional advantage of being substrate independent. Of these, the use of capping layers and ionic liquid activation are two promising techniques and will be discussed in the following sections.

2.1.4 Capping layers

In AOS TFTs, electron mobility is sensitive to defect states and therefore the mobility is expected to increase significantly by reducing the defect density. Metallic capping layers overlaid between S/D contacts reduces drain current-crowding and the carrier scattering effect due its lower value of sheet resistance[119].

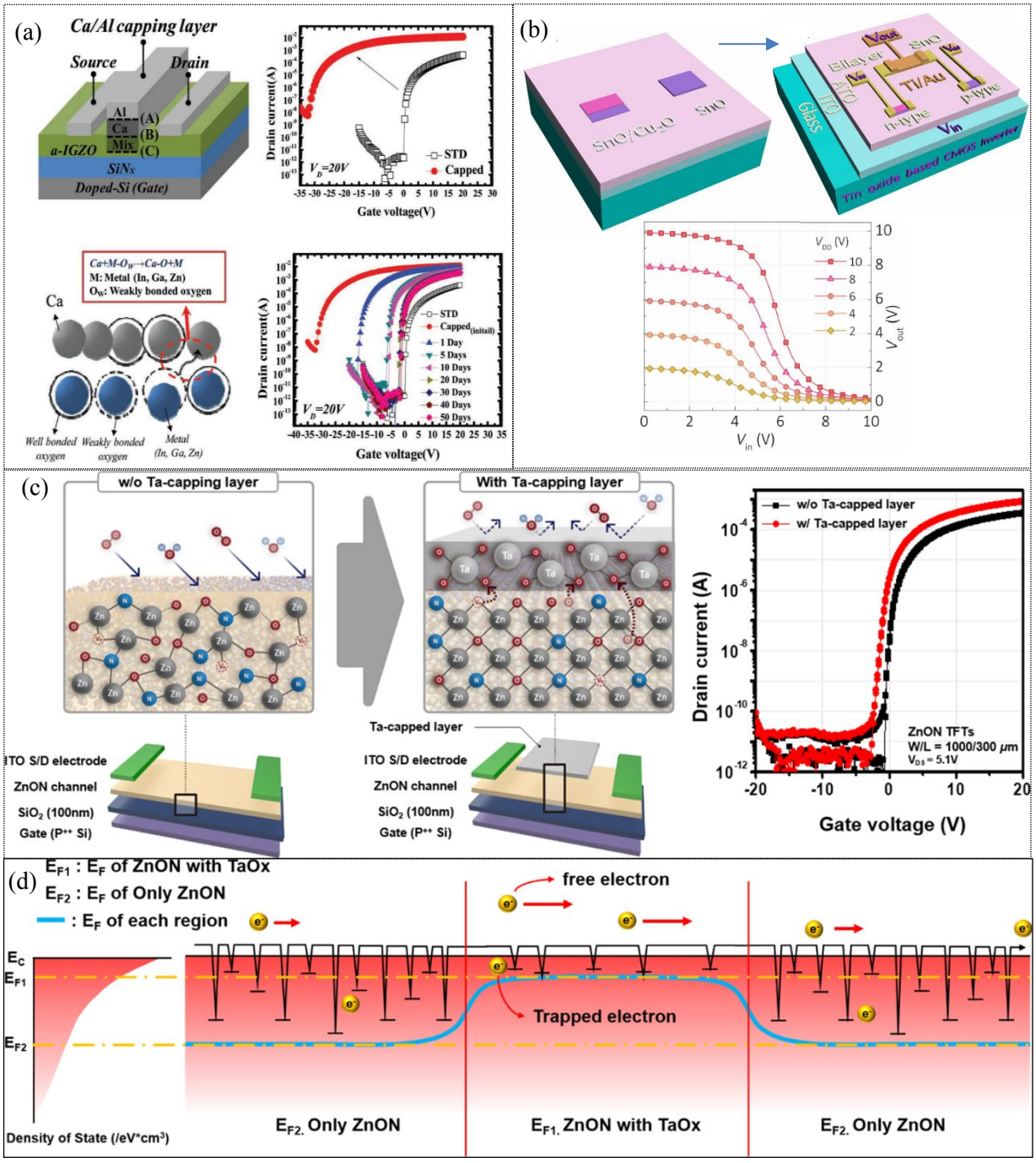

Figure 6. **(a)** Bottom-gate top-contact a-IGZO TFT (STD device) is capped with Ca/Al dual layer and transfer characteristics of STD and of Ca/Al-capped a-IGZO TFTs with 50 days storage test in air[120]. **(b)** Schematic diagram of CMOS inverters fabrication and transfer curves of optimized CMOS inverter[121]. **(c)** Schematic diagram of Ta-capped ZnON TFTs P++ silicon wafer, transfer characteristics and Schematic energy-band diagram dictated by trap-limited conduction (TLC) modulation for the Ta-capped ZnON TFTs[123]

Additionally, the proposed devices effectively prevent the adsorption/desorption reaction of ambient oxygen and hydrogen molecules on the surface. This structure has shown high μ_{FE} as well as enhanced stability simply by adopting a metal capping layer[120]. In 2012 H.-W. Zan et al. demonstrated an amorphous Indium-Gallium-Zinc Oxide (a-IGZO) TFT with double capping layer of metal calcium/ aluminium at its back channel (Fig. 6a). The mobility of the TFT increased from 12 to 160 $cm^2 V^{-1} s^{-1}$ after deposition of the capping layer of Ca/Al. The Ca layer (150 µm long, 35 nm thick) deposited on the back channel of these devices served as the mobility enhancement capping layer while the Al layer deterred the formation of CaO, $Ca(OH)_2$ and $CaCO_3$ by absorption of oxygen, water and carbon dioxide respectively from the atmosphere. The Ca atoms close to the IGZO layer reacts with weakly bonded oxygen atoms of the Zn-O, In-O, and Ga-O to form Ca-O bonds and enhances the field effect mobility of the device due to reduction of defect density[120]. In 2015 Z. Wang et al. successfully demonstrated facile fabrication of a CMOS inverter at low temperature by using single-step deposition of the tin mono-oxide channel layer (Fig. 6b). Selective deposition of a copper oxide capping layer on top of the tin mono-oxide, provided additional oxygen to form an n-type SnO_2 phase at temperature as low as 190°C in air. The phase transition from SnO to SnO_2 typically

occurs at temperature above 300℃. However, in the case of bilayer system this can occur at temperatures as low as 190℃[121]. In 2017, Y. Shin et. al showed low-temperature crystallization of IGZO using a tantalum (Ta) catalytic layer. The field-effect mobility was significantly boosted to 54.0 $cm^2 V^{-1} s^{-1}$ for the IGZO device with a metal induced polycrystalline channel formed at 300 °C as compared to 18.1 $cm^2 V^{-1} s^{-1}$ for the non- catalysed IGZO TFT. A 20 nm thick Ta thin film, serving as the crystallization catalytic layer, was sputtered selectively through a shadow mask on top of the active layer between the source and drain electrodes. Improvement in the device mobility occurred because Ta acted as a catalyst to break weak IGZO bonds, and these broken bonds within IGZO rearrange to form crystallized regions during thermal annealing[122]. In 2019, T. Kim and co-workers also investigated novel TaO_x encapsulation to enhance performance of ZnO:N thin-film transistors (Fig. 6c). A 10 nm thick Ta film was selectively deposited and annealed at 200 °C for 1 h under O_2 ambient. Ta capped TFTs (μ_{FE} = 89.4 $cm^2 V^{-1} s^{-1}$, V_{th} = - 0.45 V, $I_{ON}/_{OFF}$ = 8.6 x 10^8) showed improved performance when compared to uncapped TFTs (μ_{FE} = 36.2 $cm^2 V^{-1} s^{-1}$, V_{th} = 1.28 V, $I_{ON}/_{OFF}$ = 2.9 x 10^8) by scavenging and passivation effects of the TaO_x film which occurred due to facile elevation of the quasi-Fermi level as a result of a lower acceptor-like trap state distribution and large carrier concentration value. Smaller number of sub-gap states near the conduction band (CB) minimum and a higher net carrier density for the TaO_x-capped devices, increased the fermi energy level toward the CB edge under thermal equilibrium conditions, thus leading to efficient band conduction and fast carrier transport under the on-state condition[123].

2.1.5 Ionic liquid Approach/ or Electric field driven approaches

Owing to capability to generate extremely high electrostatic field (~50MV/mm^{-1}), ionic liquid (IL) gating has been extensively used to investigate electrostatic effects on fundamental physics problems in strongly correlated systems. These extremely high electric fields can extract or intercalate ionic species out of or into solids. Thus manipulation of the oxygen vacancy concentration via IL gating is a promising approach to tune the electrical properties, mitigating the need for high temperature annealing[124,125]. In 2019, Kulkarni et. al. demonstrated athermal activation in IWO channel TFT via an electrolyte-gating approach. Room temperature, RF sputtered IWO thin films (thickness ~ 7 nm) on SiO_2/Si wafers and on flexible substrate were activated by EMIM TFSI (1-Ethyl-3-methylimidazolium bis(trifluoromethylsulfonyl)imide) ionic liquids. This technique facilitated activation of non-functioning TFT to a working transistor with mobility of μ_{FE} = 7.1 $cm^2 V^{-1} s^{-1}$, $I_{ON}/_{OFF}$ = 10^6 (back gate) and ionic-gated transistors with μ_{FE} = 105.4 $cm^2 V^{-1} s^{-1}$ on flexible substrates at room temperature. Modulation of the local electronic structure of the channel by migrating oxygen species across the semiconductor–dielectric interface generated enough carriers for charge transport and for activation of oxygen-compensated thin films[124]. In 2016, Pudasaini et. al. demonstrated IL gating of a-IGZO with 1-hexyl-3-methylimidazolium bis (trifluoromethylsulfonyl) imide ([Hmim][TFSI]) ionic liquid to modulate oxygen concentration in the channel layer and tune the threshold voltage (V_{th}). The ionic liquid was dispensed to cover the a-IGZO active area and auxiliary gate electrode as shown in Fig. 7b. The strong electric field induced by the electrical-double layer (EDL) formed at the interface between the IL and a-IGZO surface was responsible for the extraction of oxygen in the IGZO layer. A relatively large ON current (≈50 μA) with a $I_{ON}/_{OFF}$ =10^5 and μ_{FE} = 23.2 $cm^2 V^{-1} s^{-1}$ was achieved for the athermal activated IL side gated a-IGZO TFT[125]. In 2013 J. Jeong et. al. showed an electrolyte gating approach which suppresses the metal-to-insulator transition and stabilizes the metallic phase to temperatures below 5 kelvin for epitaxial thin films of VO_2, even after the ionic liquid was completely removed. These large electrostatic fields have been shown to be capable of moving ions in/out of other oxides as well (VO_2, $SrTiO_3$)[126]. In 2011 K. Ueno et. al. demonstrated an unexpected superconducting phase in $KTaO_3$ by ionic gating approach. EDL transistor devices were fabricated on $KTaO_3$ single crystals with an ionic liquid (as shown in Fig. 7a) with high $I_{ON}/I_{OFF} > 1\times10^5$. After biasing the ionic gate, Electrostatic carrier doping could induce superconductivity in $KTaO_3$ [127]. This novel oxygen vacancy modulation techniques facilitate low temperature activation of devices on flexible substrate. However, modulation of oxygen vacancies is still debated. As some researchers continue to suspect the changes to be related to movements of other ions (H^+, OH^-) present in ionic liquid[128]. Since electronic gating utilising a liquid on top of the device may not be practical, researchers are also exploring ionic gels.

2.2 Chemical routes for reduction of process temperature

For solution-processed metal oxide films deposited from precursor solutions, the as-deposited thin films consists of metal cation complexes, hydroxides, oxides etc. During the subsequent high temperature anneal, the M-O-M network is formed through condensation process and complete anion decomposition and organic residue removal. If insufficient thermal energy is available for the consumption of hydroxides and the decomposition of anions, the M-O-M structure formation and oxygen vacancy formation is affected and excess trap sites are generated, leading to degraded TFT device characteristics.

2.2.1 Precursor and solvent selection

For the precursor route of metal oxide film formation for MO thin film transistors, the choice of precursor and solvent plays a vital role on the structural and electrical properties of the resultant metal oxide film. Figure of merits of a TFT such as the mobility, subthreshold swing and threshold voltage are predominantly influenced by the physical properties of the films such as, M-O, M-OH and oxygen vacancy content, density, defect concentration, presence of impurities etc and these are in-turn dependent on the precursors and solvent utilized. Of the various metal precursors available, chlorides, acetates and nitrates have been widely adopted for the formation of metal oxide films[129]. A comprehensive study has been conducted by Kim et al, to investigate and analyze the effect of precursors and solvent on MO TFTs[130]. The mobility and the

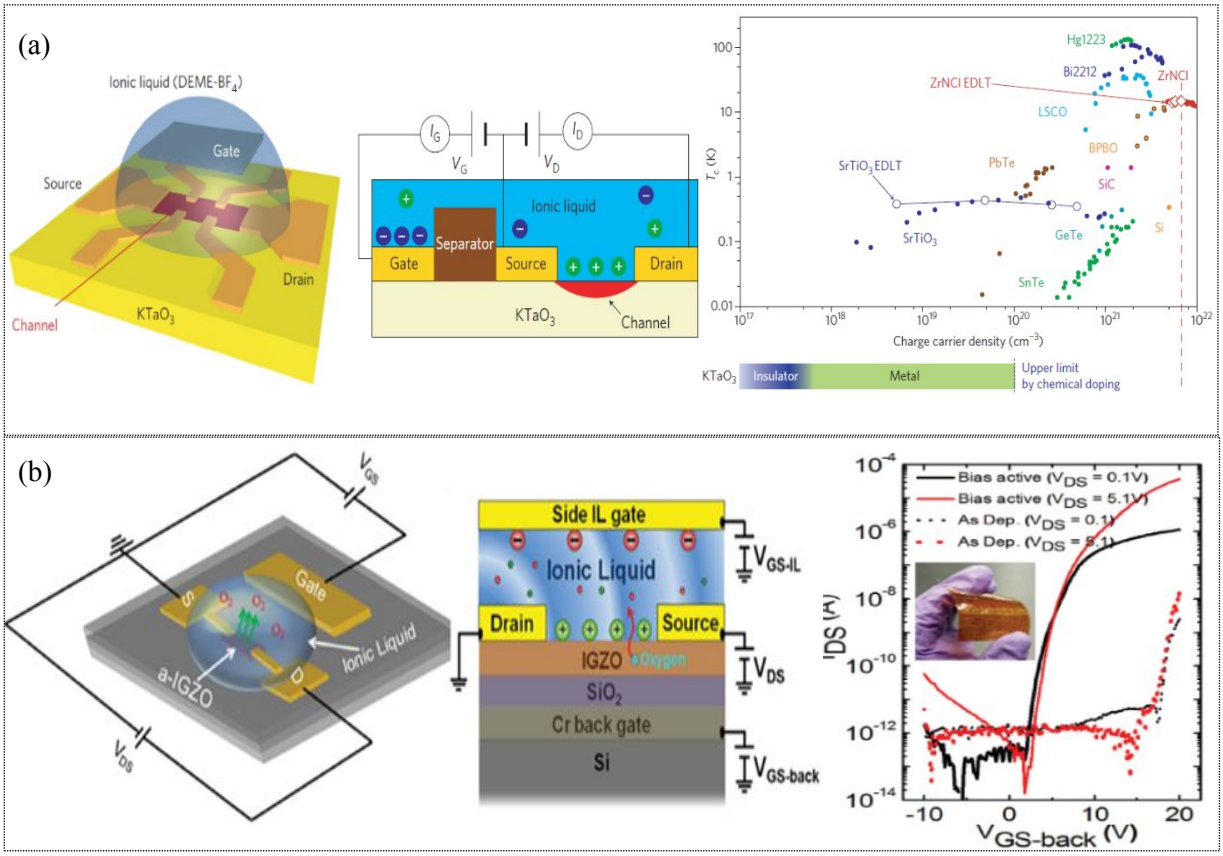

Figure 7 **(a)** Electric double-layer (EDL) $KTaO_3$ transistor and Superconducting critical temperature Tc as a function of three-dimensional charge carrier density for chemically doped superconductivity in 11 different material systems (filled symbols), and electrostatically induced superconductivity in two of these (open symbols)[127]. **(b)** Dual-side gated a-IGZO TFT on a silicon substrate used for field induced activation testing and transfer characteristics of IL gate activated flexible IGZO TFT[125]

threshold voltage of the fabricated MO TFTs are influenced by type of precursor and type of solvent respectively (Fig. 8a). Analytical studies proved that precursor type affected the trap density and also the band mobility, which is an indication of s orbital overlap, while the solvent, which determines the metal-ion complex formed in the precursor solution, affected the deep level traps, dependent on the number of metal interstitials. Of the various precursors, nitrate-based MO-films demonstrated the highest field-effect mobility and lowest trap density, while use of acetonitrile as the solvent lead to the highest threshold voltage. XPS investigations corroborated the findings and illustrate that the nitrate-based films display the lowest M-OH content, resulting in reduced trap density and largest M-O to M-OH bond area ratio, resulting in highest s orbital overlap. The precursor type was also found to affect the density of the film formed and hence the mobility, by virtue of the volume of the decomposed ions and atoms in the precursors. Nitrates also yielded MO films with highest density while chlorides by virtue of their inherent defects yielded MO films with the lowest density. Among the various metal precursors used such as chlorides, acetates and nitrates, the latter also has the weakest anion complexation, which ensures complete anion decomposition at lower temperatures[131]. Use of nitrate precursors thus provides an approach to reduce the thermal energy required for the formation of high-quality MO films with reduced hydrates and other M-O-M network disrupting impurities by virtue of anions capable of lower temperature decomposition, as is evident from the thermogravimetric studies (Fig. 8b). Metal alkoxides are a class of precursors, which afford the formation of metal oxide films at low temperatures in the presence of an aqueous catalyst or in an aqueous environment. H. Sirringhaus et al, have demonstrated a sol-gel on chip process using indium alkoxide cluster and zinc-bis-methoxyethoxide in which an *insitu* process utilizing a controlled amount of water vapor to facilitate the hydrolyses on the surface of the spin coated film, resulting in metal-oxide film formation at a low temperature of 230 °C with low M-OH content. The fabricated TFT exhibited a mobility of 10 $cm^2V^{-1}s^{-1}$, V_{on}=0V, high I_{on}/I_{off} (10^8) and low hysteresis with stable, repeatable performance and high operational stability[132]. Solution processed MO TFTs typically employ 2-methoxy ethanol or similar alcohol-based solvents for precursor solution. Recently, water has emerged as a contender by virtue of its ability to form carbon residue-free films at low processing temperature[133134135]. Ionic species dissociation is promoted by the high polarity and high dielectric constant (~80) of the aqueous solvent and by acting as a sigma donor, results in the formation of hexaaqua complexes as shown in Fig. 8d. Water, when used for the fabrication of both Al_2O_3 dielectric and In_2O_3 films, resulted in TFTs with mobility of ~38 $cm^2V^{-1}s^{-1}$ and I_{on}/I_{off} of 10^7 at a processing temperature of 250°C [136]. The duration and temperature at which aqueous precursors are processed before spin-coating also exhibits significant impact on the MO film formed. According to Park et. al, precursors retained at 70°C for longer durations (12-72h), have a higher concentration of dissociated cations which results in higher

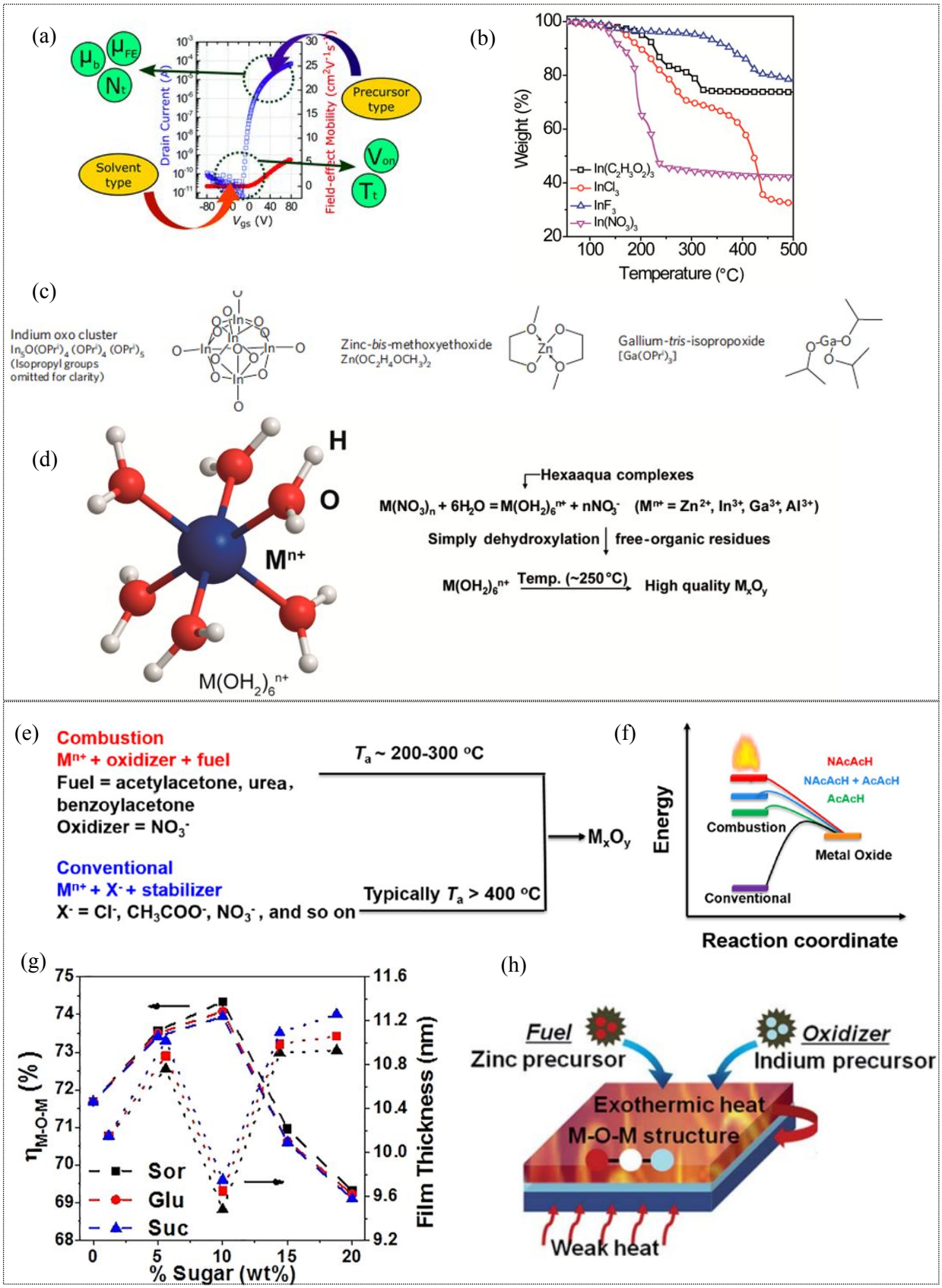

Figure 8 **(a)** Illustration of the effect of solvent and precursor type on the TFT device characteristics.[130] **(b)** Thermogravimetric analyses of the various aqueous metal precursors of $In(C_2H_3O_2)_3$, $InCl_3$, InF_3, and $In(NO_3)_3$.[134] **(b)** Various alkoxide derivatives used for metal oxide formation.[132] **(d)** Structure of the hexaaqua complexes formed in aqueous solvent and the progress of reactions resulting in the formation of metal oxide films[136] **(e)** Combustion vs conventional synthetic approaches [138] **(f)** Energetics of combustion synthesis for various fuels [143] **(g)** XPS O1s M-O-M peak area to total peak area ratio and film thickness vs. sugar concentration [144] **(h)** Schematic diagram of combustion synthesis via use of metal precursors bearing fuel and oxidizer ligands[145]

concentration of hexaaqua metal ion complexes, critical for the low temperature metal oxide formation using aqueous route[137].

2.2.2 Combustion synthesis

As discussed, in the case of solution-processed metal oxides, low temperature anneals result in incomplete metal oxide formation and hydroxyl group rich films. A universal and facile method to reduce the processing temperature of solution-processed metal oxide films viz., combustion synthesis, was demonstrated by Kim et. al, in 2011[138]. In the combustion synthesis approach, a fuel additive triggers a localized exothermic reaction with metal nitrate precursors (oxidisers), thereby providing sufficient energy to eliminate the need for a subsequent high temperature anneal for M-O-M network formation and residue removal (Fig. 8e). Acetyl acetone and urea are the commonly used fuels for combustion synthesis formation of metal oxide films[139140141142]. Facchetti et al., reported that the addition of an oxidizing NO_2 group to acetylacetone fuel results in an enthalpy of combustion of 988.6 compared to 784.4 J/g of acetyl acetone and ignition temperature of 107.8 °C compared to 166.5 °C of acetylacetone (Fig. 8f)[143]. This results in a lowering of the processing temperature for the formation of metal oxide films while simultaneously resulting in denser films with higher M-O-M content. Non-toxic and environmentally safe carbohydrates such as sorbitol, sucrose and glucose as co-fuels have been shown to be effective in increasing the enthalpy of the overall reaction[144]. Their optimized incorporation in the fuel system results in dense, smooth, high-quality metal oxide content as is clear from XPS and thickness measurement, where the M-O-M to total O1s peak ratio and film densification is highest at 10% sugar content, as shown in Fig. 8g with higher sugar content adversely affecting the film formation due to exploitation of oxidizers for excess sugar decomposition and the generation of impurities. With a prudent choice of metal precursors which can act as the source of both oxidizer and fuel (Fig. 8h), Cho et. al, has demonstrated that a self-combustion synthesis can also be activated in a two-component precursor system without the need for further fuels or additives[145]. Combustion synthesis is a viable method of reducing the processing temperature as it is independent of any additional post processing steps and is readily scalable. However, though combustion can proceed at temperatures as low as 100 °C, a higher temperature of around 200-300 °C is required to ensure adequate decomposition of the precursors to ignite the combustion, especially since the nitrates are generally the oxidizers for the combustion synthesis.

3. Other low temperature processing approaches

Plasma treatment using hydrogen, argon etc have also been used for sputtered MO films to improve the device performance under low temperature processing conditions and have also been extended to solution processed MO TFTs [146147].Plasma treatment using hydrogen has been used for the decomposition of residual organic species subsequent to the formation of metal oxide layers. This treatment followed by an oxidation step has been shown to increase the stability of the device while improving the TFT device performance [148]. There have recently been reports on the use of NH_3 and N_2O plasma treatments resulting in improved device performance [149150]. Other novel techniques include water vapour annealing [151], where the presence of water vapor leads to efficient hydrolysis reaction for solution processed MO films, resulting in higher M-O and lower M-OH concentrations and photo catalytic reactions using TiO_2 under UV irradiation for decomposition of organic residues and defect site reduction. In addition to these novel methods, a combination of various annealing conditions and techniques have been shown to result in improved performance of MO TFTs. Combining plasma treatment with (a) thermal annealing[152] (b) atmospheric pressure treatment[153] or (c) microwave irradiation[154] has been shown to drastically improve TFT performance.

4. Conclusions and outlook

Significant research effort is being dedicated to achieve low temperature processing for MO TFTs, thus enabling their widespread application in flexible electronics. Conventional annealing techniques such as high-temperature thermal annealing, rapid thermal annealing, laser annealing etc require high temperature to tune the oxygen vacancy in the metal oxide semiconductor which results in adverse effects on flexible substrates. Replacing the high thermal budget required for such conventional annealing with photochemical, plasma-assisted and microwave annealing techniques are applicable to both vacuum deposited and solution processed MO TFTs. In the case of solution processed MO films, additional possibilities are such as appropriate selection of precursors, solvents and fuel additives for aiding combustion synthesis, reducing the process temperature for the formation of high-quality metal oxide films. However, all of these techniques except for laser annealing are nonselective, i.e., all the TFTs on the substrates are affected by the process. If selective annealing is required, a complex number of steps will be required, such as photolithography, to tune the attributes of thin film semiconductor selectively. As discussed in this review, another promising alternative is the athermal oxygen vacancy modulation and defect passivation of the metal oxide film for tailoring the electronic structure, which renders high temperature treatments, typically critical for achieving high performance TFTs, dispensable. Athermal activation using capping layer or ionic liquid paves the way for flexible and transparent electronics. In the ionic liquid gating approach, which is limited to charge modulation and accumulation for ionic liquid TFT, the high electric field of the order of 50 MV/mm present at the interface due to Helmholtz layers can be used to vary the oxygen ions present in the film. The controlled manipulation of oxygen vacancies changes the conductance of film in a precise manner which is of interest for novel applications such as neuromorphic electronics. Such techniques also allow for the selective treatments on individual TFTs within a large substrate. Metal capping layer approach facilitates the decrease of weakly bonded oxygen density or reduction in the defect density by partial crystallization of underlying AOS layer at low temperature. This structure has shown high μ_{FE} as well as enhanced stability simply by adopting selective metal capping layer while ensuring reduction in the process temperature as

discussed in above sections. Apart from the options discussed in the review, manipulation of the active layer structure is another viable alternative for achieving high performance metal oxide TFT. Hybrid metal oxide-2D TFTs have been investigated, where the addition of high conductivity 2D materials, such as graphene/CNT, in the active layer stack leads to enhanced TFT mobility. Hybrid metal oxide-2D heterostructure and quasi superlattice metal oxide stacks are another class of active layers employed for realizing high mobility TFTs at low processing temperature. According to reports, the ultrathin metal oxide layers that form these active layers enable the manifestation of 2D charge transport phenomenon, while the incorporation of deep fermi level metal oxide in the stack results in higher I_{on}/I_{off} ratio. Compared to initial research studies, effort is now being made to ensure that the methods used for enhanced device performance at lower processing temperatures do not adversely affect the device stability. Metal oxide semiconductors are also highly sensitive to atmosphere, where exposure to moisture and oxygen can affect device stability; an issue which needs to be addressed. As discussed, researchers have reported that using capping layers, such as Al_2O_3, SiO_2, Y_2O_3, HfO_2, ZrO_2,TiO_2, AHO (Al_2O_3-HfO_2 stack) and ATO (Al_2O_3, TiO_2 stack) can improve the stability of oxide semiconductor in air and at higher temperatures. In addition, the scalability and production-line compatibility of the various techniques for reducing the processing temperature of metal oxide semiconductors should also be thoroughly examined. With continued research efforts being deployed in realizing stability, scalability and low temperature processing, metal oxide thin films are the most promising material system for propelling the flexible and transparent electronics into a ubiquitous technology.

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